

## ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device includes: a substrate; a first conductivity type of semiconductor layers arranged above the substrate as being insulated from the substrate and insulated from each other; cell transistors formed on the respective semiconductor layers, each of which has a second conductivity type of source, drain layers and a gate electrode to store data in a channel body thereof corresponding to an accumulation state of majority carriers; and the first conductivity type of emitter layers formed in the respective semiconductor layers to be contacted to the respective drain layers of the cell transistors so as to constitute PN junctions therebetween, the emitter layers serving for injecting majority carriers into the respective channel bodies of the cell transistors.